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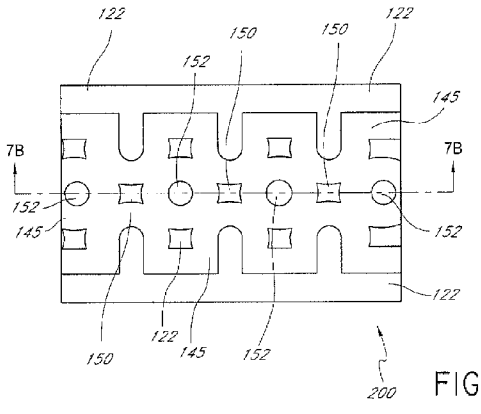


FIG. 7A

(57) Abstract: Methods are disclosed, such as those involving increasing the density of isolated features in an integrated circuit (200). Also disclosed are structures associated with the methods. In one or more embodiments, contacts are formed on pitch with other structures, such as conductive interconnects. The interconnects may be formed by pitch multiplication. To form the contacts, in some embodiments, a pattern corresponding to some of the contacts is formed in a selectively definable material (130) such as photoresist. The features (131, 134) in the selectively definable material (130) are trimmed to desired dimensions. Spacer material (140) is blanket deposited over the features (131, 134) in the selectively definable material (130) and the deposited material (140) is then etched to leave spacers (145) on sides of the features (131, 134). The selectively definable material (130) is removed to leave a mask defined by the spacer material (140). The pattern defined by the spacer material (140) may be transferred to a substrate, to form on pitch contacts. In some embodiments, the on pitch contacts may be used to electrically contact conductive interconnects in the substrate.

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